

## SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 6 GHz

### Typical Applications

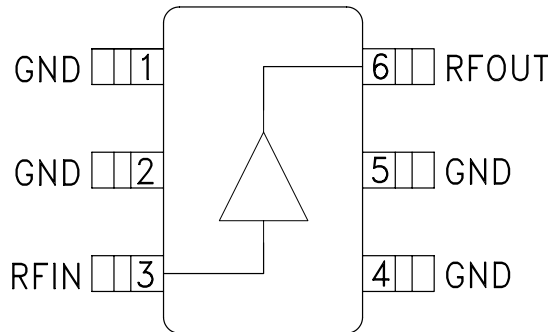
The HMC474SC70(E) is an ideal for:

- Cellular / PCS / 3G
- WiBro / WiMAX / 4G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment

### Features

- Gain: 15 dB
- P1dB Output Power: +8 dBm
- Output IP3: +20 dBm
- Cascadable 50 Ohm I/Os
- Single Supply: +3V to +10V
- Industry Standard SC70 Package

### Functional Diagram



### General Description

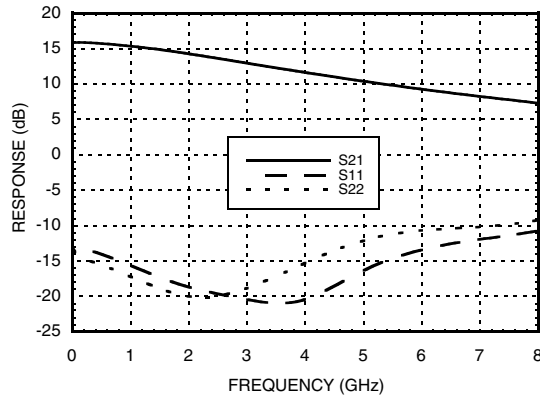
The HMC474SC70(E) is a general purpose SiGe Heterojunction Bipolar Transistor (HBT) Gain Block MMIC SMT amplifier covering DC to 6 GHz. This industry standard SC70 packaged amplifier can be used as a cascadable 50 Ohm RF/IF gain stage with up to +8 dBm output power. The HMC474SC70(E) offers 15 dB of gain with a +20 dBm output IP3 at 850 MHz while requiring only 25 mA from a single positive supply as low as +3V. The Darlington topology results in reduced sensitivity to normal process variations and excellent gain stability over temperature while requiring a minimal number of external bias components.

### Electrical Specifications, $V_s = 5V$ , $R_{bias} = 110 \text{ Ohm}$ , $T_A = +25^\circ \text{ C}$

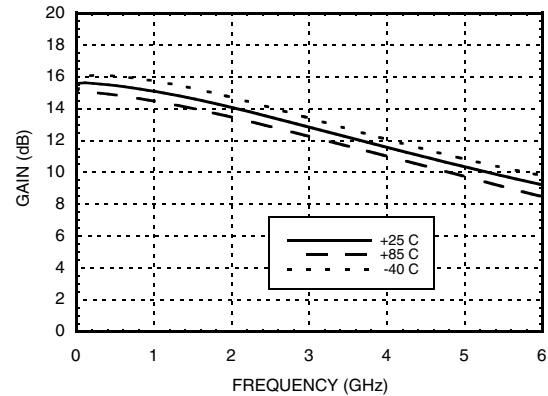
| Parameter                                                                   |               | Min. | Typ. | Max.  | Units  |
|-----------------------------------------------------------------------------|---------------|------|------|-------|--------|
| Gain                                                                        | DC - 2.0 GHz  | 12   | 15   |       | dB     |
|                                                                             | 2.0 - 4.0 GHz | 10   | 13   |       | dB     |
|                                                                             | 4.0 - 6.0 GHz | 7    | 10   |       | dB     |
| Gain Variation Over Temperature                                             | DC - 6 GHz    |      | 0.01 | 0.015 | dB/ °C |
| Input Return Loss                                                           | DC - 5 GHz    |      | 15   |       | dB     |
|                                                                             | 5.0 - 6.0 GHz |      | 14   |       | dB     |
| Output Return Loss                                                          | DC - 5 GHz    |      | 15   |       | dB     |
|                                                                             | 5.0 - 6.0 GHz |      | 12   |       | dB     |
| Reverse Isolation                                                           | DC - 6 GHz    |      | 17   |       | dB     |
| Output Power for 1 dB Compression (P1dB)                                    | 0.5 - 4.0 GHz | 5    | 8    |       | dBm    |
|                                                                             | 5.0 - 6.0 GHz | 3    | 6    |       | dBm    |
| Output Third Order Intercept (IP3)<br>(Pout= 0 dBm per tone, 1 MHz spacing) | DC - 5 GHz    |      | 20   |       | dBm    |
|                                                                             | 5.0 - 6.0 GHz |      | 18   |       | dBm    |
| Noise Figure                                                                | DC - 5 GHz    |      | 3    |       | dB     |
|                                                                             | 5.0 - 6.0 GHz |      | 3.9  |       | dB     |
| Supply Current (Icq)                                                        |               |      | 25   | 33    | mA     |

Note: Data taken with broadband bias tee on device output.

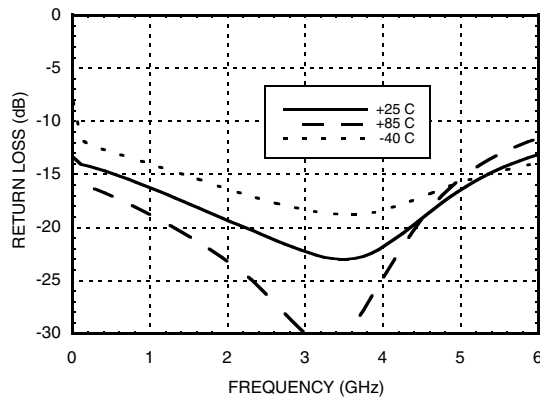
**Broadband Gain & Return Loss**



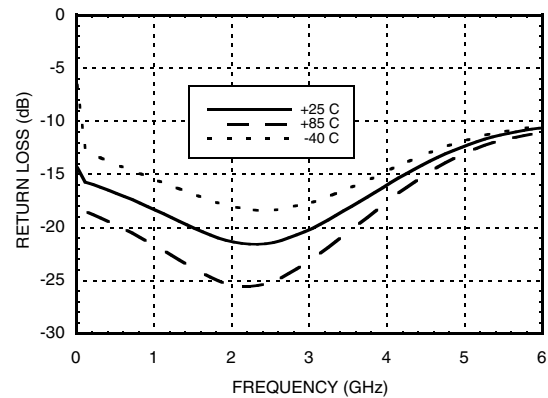
**Gain vs. Temperature**



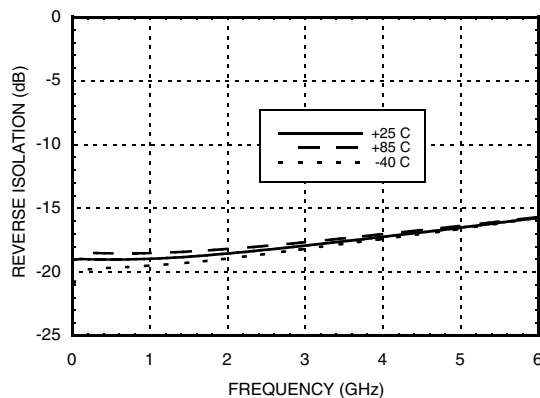
**Input Return Loss vs. Temperature**



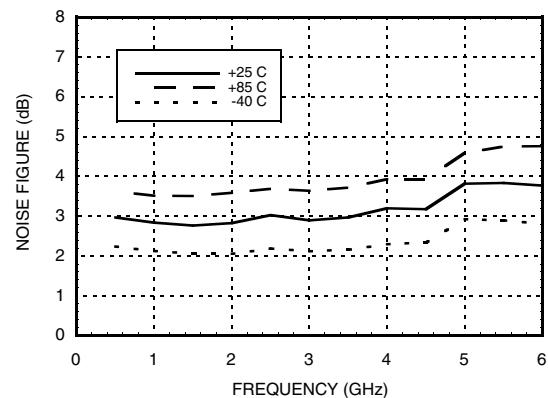
**Output Return Loss vs. Temperature**



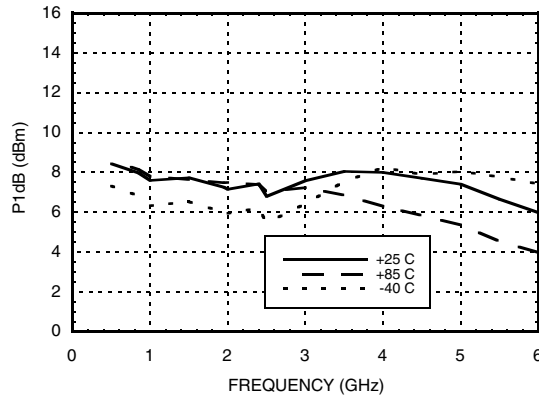
**Reverse Isolation vs. Temperature**



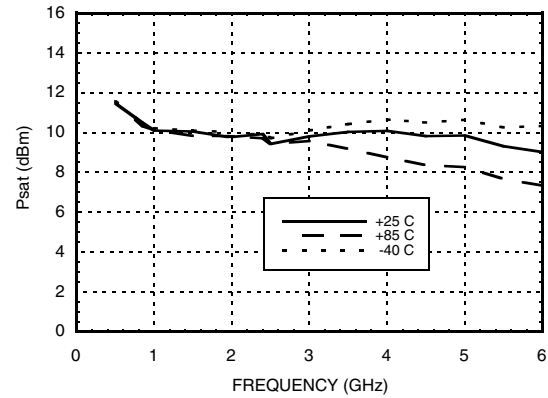
**Noise Figure vs. Temperature**



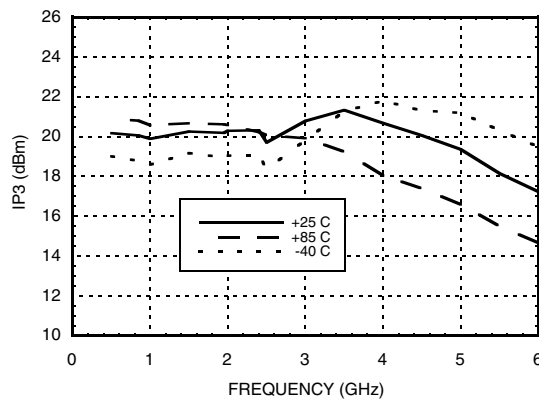
**P1dB vs. Temperature**



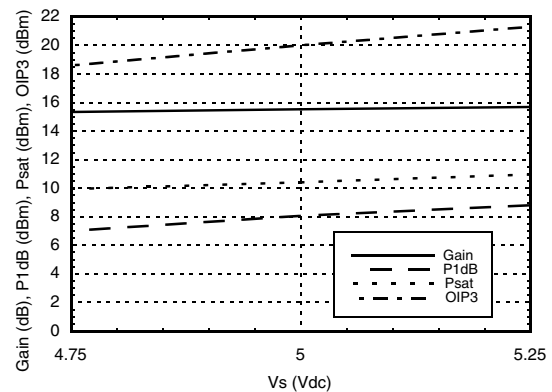
**Psat vs. Temperature**



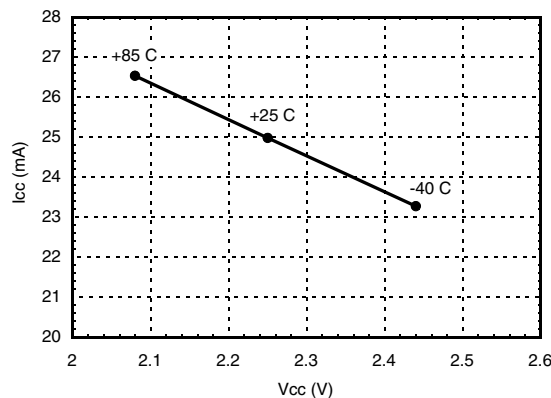
**Output IP3 vs. Temperature**



**Gain, Power & OIP3 vs. Supply Voltage  
for Rs= 110 Ohms @ 850 MHz**



**Icc vs. Vcc Over Temperature for  
Fixed Vs= 5V, R<sub>BIAS</sub>= 110 Ohms**



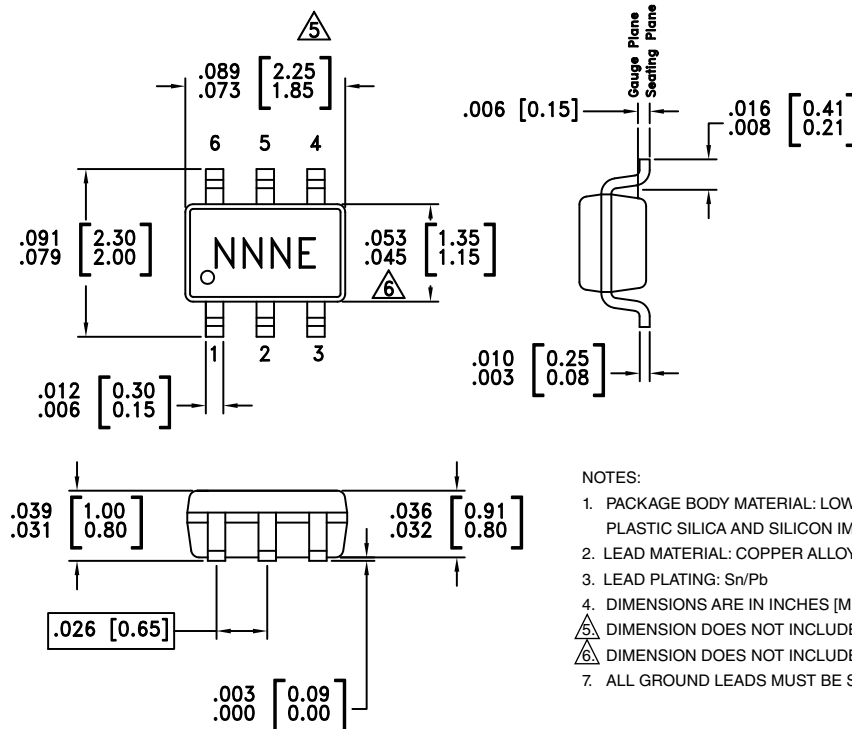
### Absolute Maximum Ratings

|                                                                            |                |
|----------------------------------------------------------------------------|----------------|
| Collector Bias Voltage (Vcc)                                               | +6.0 Vdc       |
| Collector Bias Current (Icc)                                               | 35 mA          |
| RF Input Power (RFIN)(Vcc = +2.4 Vdc)                                      | +5 dBm         |
| Junction Temperature                                                       | 150 °C         |
| Continuous P <sub>diss</sub> (T = 85 °C)<br>(derate 4.3 mW/°C above 85 °C) | 0.280 W        |
| Thermal Resistance<br>(junction to lead)                                   | 232 °C/W       |
| Storage Temperature                                                        | -65 to +150 °C |
| Operating Temperature                                                      | -40 to +85 °C  |
| ESD Sensitivity (HBM)                                                      | Class 1B       |



**ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS**

### Outline Drawing



### Package Information

| Part Number | Package Body Material                              | Lead Finish   | MSL Rating          | Package Marking |
|-------------|----------------------------------------------------|---------------|---------------------|-----------------|
| HMC474SC70  | Low Stress Injection Molded Plastic                | Sn/Pb         | MSL1 <sup>[1]</sup> | 474E            |
| HMC474SC70E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 <sup>[2]</sup> | 474E            |

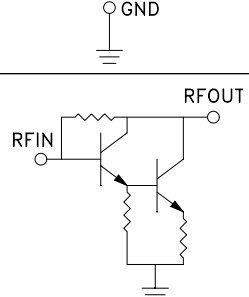
[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

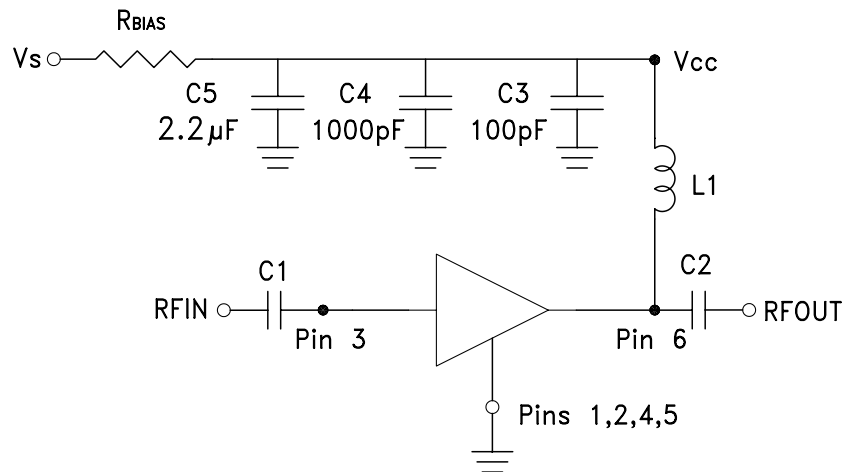
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## Pin Descriptions

| Pin Number | Function | Description                                                               | Interface Schematic                                                                 |
|------------|----------|---------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1, 2, 4, 5 | GND      | These pins must be connected to RF/DC ground.                             |  |
| 3          | RFIN     | This pin is DC coupled.<br>An off chip DC blocking capacitor is required. |                                                                                     |
| 6          | RFOUT    | RF output and DC Bias (Vcc) for the output stage.                         |                                                                                     |

## Application Circuit



## Recommended Bias Resistor Values for $I_{cc} = 25 \text{ mA}$ , $R_{bias} = (V_s - V_{cc}) / I_{cc}$

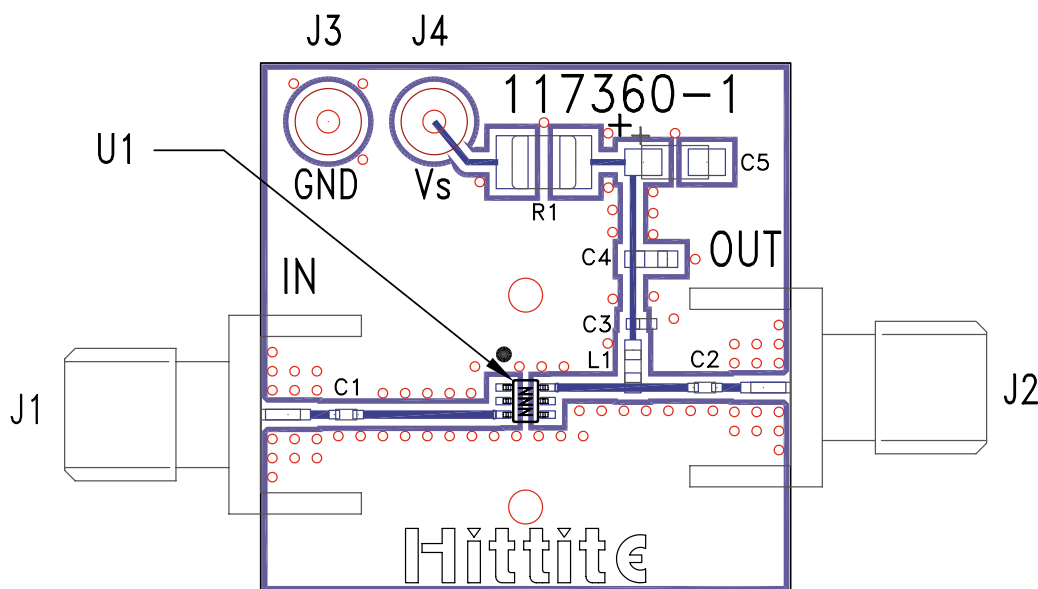
| Supply Voltage (Vs) | 3V    | 5V    | 6V    | 8V    | 10V   |
|---------------------|-------|-------|-------|-------|-------|
| RBIAS VALUE         | 30 Ω  | 110 Ω | 150 Ω | 240 Ω | 300 Ω |
| RBIAS POWER RATING  | 1/8 W | 1/8 W | 1/4 W | 1/2 W | 1/2 W |

### Note:

- External blocking capacitors are required on RFIN and RFOUT.
- RBIAS provides DC bias stability over temperature.

## Recommended Component Values for Key Application Frequencies

| Component | Frequency (MHz) |        |        |        |        |        |        |        |
|-----------|-----------------|--------|--------|--------|--------|--------|--------|--------|
|           | 50              | 900    | 1900   | 2200   | 2400   | 3500   | 5200   | 5500   |
| L1        | 270 nH          | 56 nH  | 18 nH  | 18 nH  | 15 nH  | 8.2 nH | 6.8 nH | 3.3 nH |
| C1, C2    | 0.01 μF         | 100 pF | 100 pF | 100 pF | 100 pF | 100 pF | 100 pF | 100 pF |

**Evaluation PCB**

**List of Materials for Evaluation PCB 117596 <sup>[1]</sup>**

| Item               | Description                     |
|--------------------|---------------------------------|
| J1 - J2            | PCB Mount SMA Connector         |
| J3 - J4            | DC Pin                          |
| C1 - C3            | 100 pF Capacitor, 0402 Pkg.     |
| C4                 | 1000 pF Capacitor, 0603 Pkg.    |
| C5                 | 2.2 $\mu$ F Capacitor, Tantalum |
| R1                 | 110 Ohm Resistor, 1210 Pkg.     |
| L1                 | 18 nH Inductor, 0603 Pkg.       |
| U1                 | HMC474SC70(E)                   |
| PCB <sup>[2]</sup> | 117360 Evaluation PCB           |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.